



BDX62 – A – B – C

PNP SILICON DARLINGTON POWER TRANSISTOR

The BDX62, BDX62A, BDX62B and BDX62C are mounted in TO-3 metal package. High current power darlington designed for power amplification and switching applications. The complementary NPN are BDX63, BDX63A, BDX63B, BDX63C. Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit	
V_{CEO}	Collector-Emitter Voltage		BDX62	-60	V
			BDX62A	-80	
			BDX62B	-100	
			BDX62C	-120	
V_{CEV}	Collector-Emitter Voltage	$V_{BE} = -1.5 V$	BDX62	-60	V
			BDX62A	-80	
			BDX62B	-100	
			BDX62C	-120	
V_{EBO}	Emitter-Base Voltage		-5.0	V	
I_C	Collector Current		$I_{C(RMS)}$	-8	A
			I_{CM}	-12	
I_B	Base Current		-0.15	A	
P_T	Power Dissipation	@ $T_C = 25^\circ$	90	W	
T_J	Junction Temperature		-55 to +200	$^\circ C$	
T_S	Storage Temperature				

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-C}	Thermal Resistance, Junction to Case	1.94	$^\circ C/W$

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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)		Min	Typ	Max	Unit
$V_{CEO(SUS)}$	Collector-Emitter Breakdown Voltage (*)	$I_C = -0.1$ A $I_B = 0$ $L = 25$ mH	BDX62	-60	-	-	V
			BDX62A	-80	-	-	
			BDX62B	-100	-	-	
			BDX62C	-120	-	-	
I_{CEO}	Collector Cutoff Current	$V_{CE} = -30$ V $V_{CE} = -40$ V $V_{CE} = -50$ V $V_{CE} = -60$ V	BDX62	-	-	-0.5	mA
			BDX62A	-	-		
			BDX62B	-	-		
			BDX62C	-	-		
I_{EBO}	Emitter Cutoff Current	$V_{BE} = -5$ V	BDX62	-	-	-5.0	mA
			BDX62A				
			BDX62B				
			BDX62C				
I_{CBO}	Collector-Base Cutoff Current	$V_{CBO} = -60$ V	BDX62	-	-	-0.2	-
		$V_{CBO} = -40$ V $T_{CASE} = 200^\circ$ C		-	-	-2	
		$V_{CBO} = -80$ V	BDX62A	-	-	-0.2	
		$V_{CBO} = -50$ V $T_{CASE} = 200^\circ$ C		-	-	-2	
		$V_{CBO} = -100$ V	BDX62B	-	-	-0.2	
		$V_{CBO} = -60$ V $T_{CASE} = 200^\circ$ C		-	-	-2	
		$V_{CBO} = -120$ V	BDX62C	-	-	-0.2	
		$V_{CBO} = -70$ V $T_{CASE} = 200^\circ$		-	-	-2	
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C = -3.0$ A $I_B = -12$ mA	BDX62	-	-	-2	V
			BDX62A				
			BDX62B				
			BDX62C				
V_F	Forward Voltage (pulse method)	$I_F = 3$ A	BDX62	-	-	-2.5	V
			BDX62A				
			BDX62B				
			BDX62C				
V_{BE}	Base-Emitter Voltage (*)	$I_C = -3.0$ A $V_{CE} = -3$ V	BDX62	-	-	-	V
			BDX62A				
			BDX62B				
			BDX62C				



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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

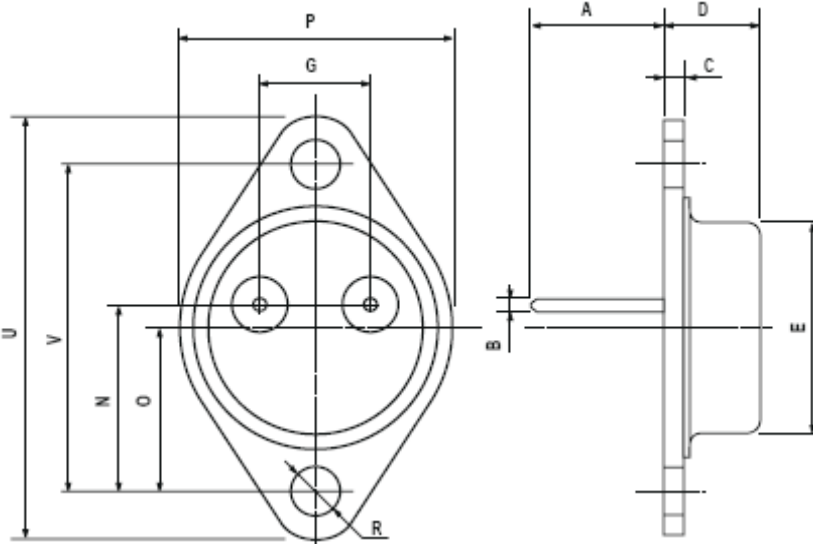
Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit	
f_{hfe}	Cut-off frequency	$V_{CE}=3\text{ V}$ $I_C=3\text{ A}$	BDX62	-	100	-	kHz
			BDX62A				
			BDX62B				
			BDX62C				
f_T	Transition Frequency	$V_{CE}=-3\text{ V}$, $I_C=-3\text{ A}$ $f=1\text{ MHz}$	BDX62	-	7	-	MHz
			BDX62A				
			BDX62B				
			BDX62C				
h_{FE}	D.C. current gain (*)	$V_{CE}=-3\text{ V}$, $I_C=-0.5\text{ A}$	BDX62	-	1500	-	-
			BDX62A				
			BDX62B				
			BDX62C				
		$V_{CE}=-3\text{ V}$, $I_C=-3\text{ A}$	BDX62	1000	-	-	
			BDX62A				
			BDX62B				
			BDX62C				
		$V_{CE}=-3\text{ V}$, $I_C=-8\text{ A}$	BDX62	-	750	-	
			BDX62A				
			BDX62B				
			BDX62C				

(*) Pulse Width $\approx 300\ \mu\text{s}$, Duty Cycle $\angle 2.0\%$

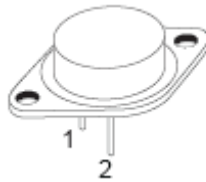
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MECHANICAL DATA CASE TO-3

DIMENSIONS (mm)		
	min	max
A	11	13.10
B	0.97	1.15
C	1.5	1.65
D	8.32	8.92
F	19	20
G	10.70	11.1
N	16.50	17.20
P	25	26
R	4	4.09
U	38.50	39.30
V	30	30.30



Pin 1 :	Base
Pin 2 :	Emitter
Case :	Collector



Revised September 2012

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